

- Logic-Level Gate Drive
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

Description

Fifth Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application. The through-hole version (IRL1004L) is available for low-profile application.

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ^⑥	130 ^⑤	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ^⑥	92 ^⑤	
I_{DM}	Pulsed Drain Current ^{①⑥}	520	
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy ^⑥	700	mJ
I_{AR}	Avalanche Current ^①	78	A
E_{AR}	Repetitive Avalanche Energy ^①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ^{③⑥}	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

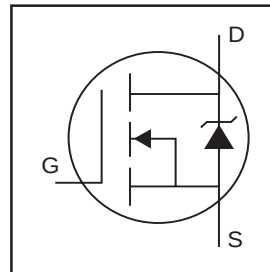
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)*	—	40	

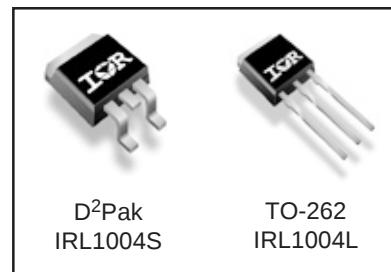
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HEXFET® Power MOSFET



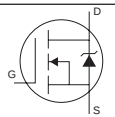
$V_{DSS} = 40V$
$R_{DS(on)} = 0.0065\Omega$
$I_D = 130A$ ^⑤



Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.04	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.0065	Ω	$V_{GS} = 10V, I_D = 78A$ ④
		—	—	0.009		$V_{GS} = 4.5V, I_D = 65A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	63	—	—	S	$V_{DS} = 25V, I_D = 78A$ ⑥
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 32V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	100	nC	$I_D = 78A$
Q_{gs}	Gate-to-Source Charge	—	—	32		$V_{DS} = 32V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	43		$V_{GS} = 4.5V$, See Fig. 6 and 13 ④⑥
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 20V$,
t_r	Rise Time	—	210	—		$I_D = 78A$,
$t_{d(off)}$	Turn-Off Delay Time	—	25	—		$R_G = 2.5\Omega$,
t_f	Fall Time	—	14	—		$R_D = 0.18\Omega$, See Fig. 10 ④⑥
L_S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	—	5330	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1480	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	320	—		$f = 1.0MHz$, See Fig. 5⑤⑥

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode) ②	—	—	130 ⑤	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①②	—	—	520		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 78A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	78	120	ns	$T_J = 25^\circ\text{C}, I_F = 78A$
Q_{rr}	Reverse Recovery Charge	—	180	270	nC	$di/dt = 100A/\mu s$ ④⑥
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
 - ② Starting $T_J = 25^\circ\text{C}$, $L = 0.23mH$
 $R_G = 25\Omega$, $I_{AS} = 78A$. (See Figure 12)
 - ③ $I_{SD} \leq 78A$, $di/dt \leq 370A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$
 - ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
 - ⑤ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handing of the package refer to Design Tip # 93-4
 - ⑥ Uses IRL1004 data and test conditions
- * When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

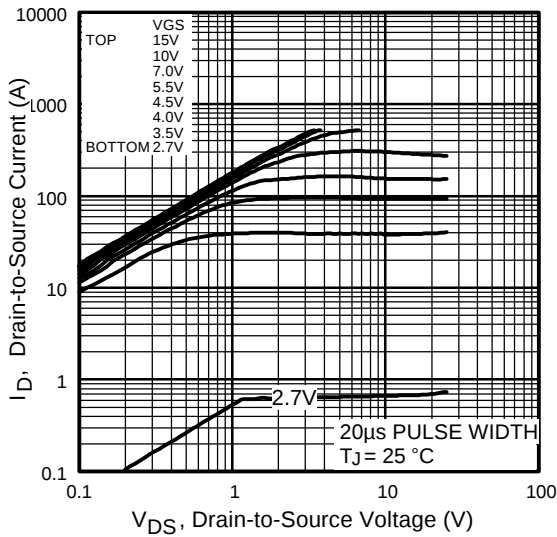


Fig 1. Typical Output Characteristics

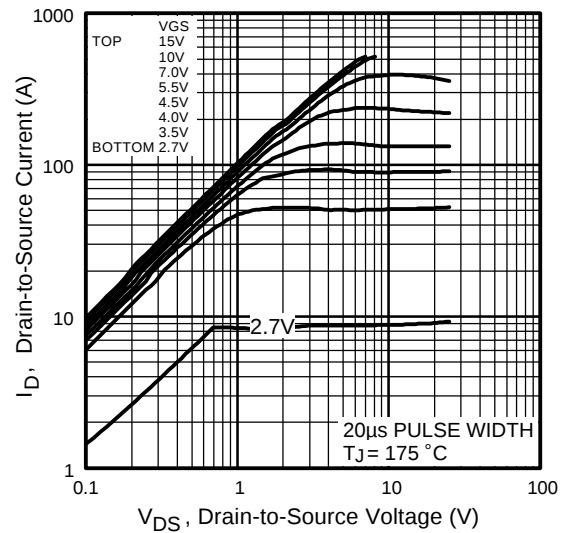


Fig 2. Typical Output Characteristics

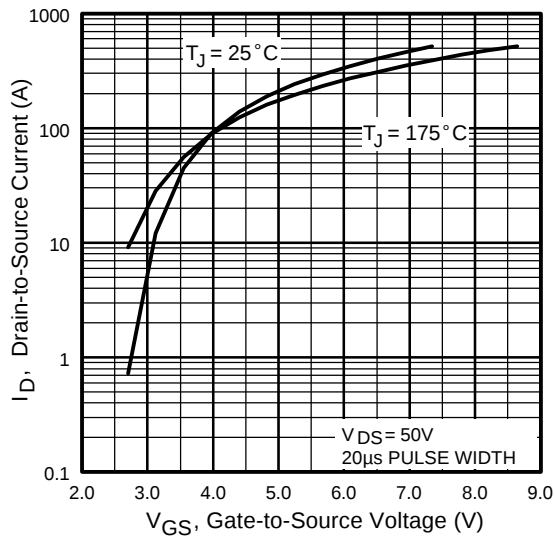


Fig 3. Typical Transfer Characteristics

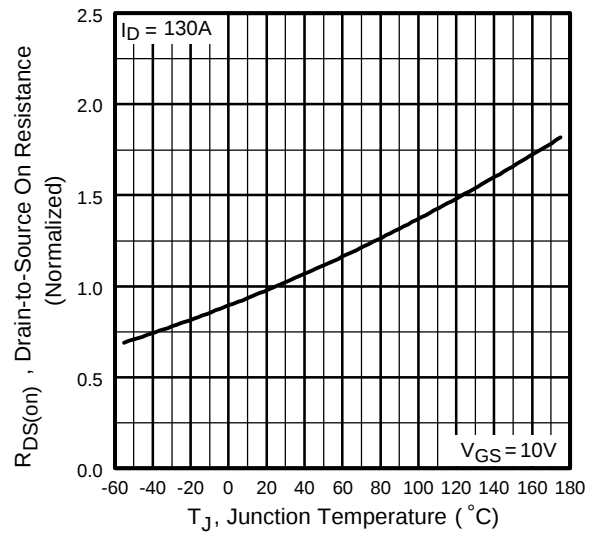


Fig 4. Normalized On-Resistance Vs. Temperature

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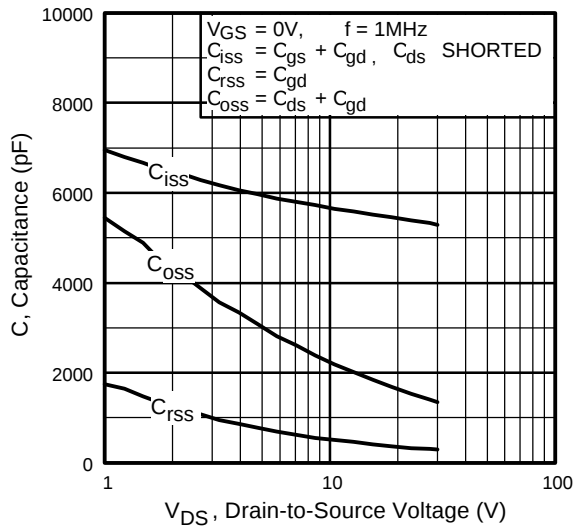


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

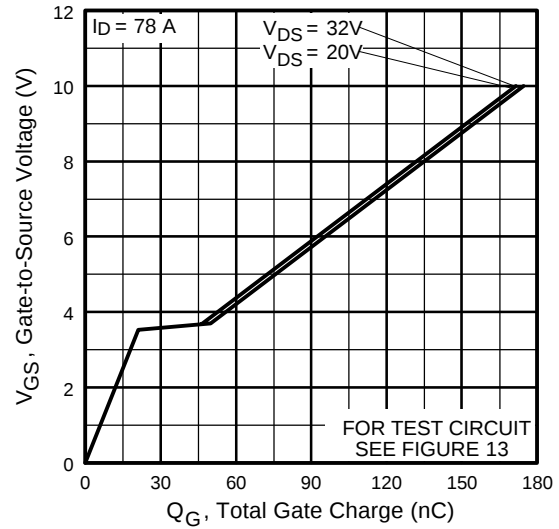


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

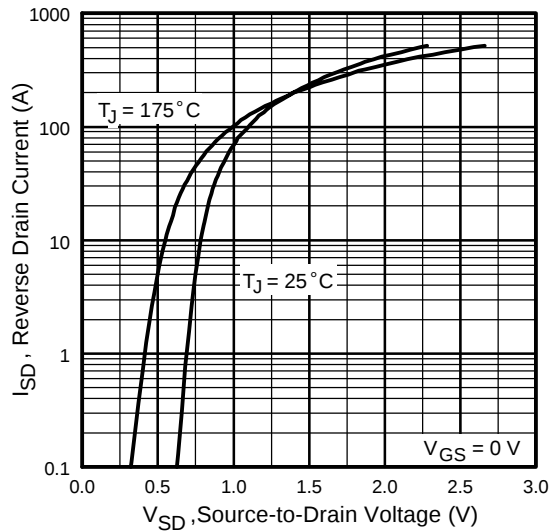


Fig 7. Typical Source-Drain Diode Forward Voltage

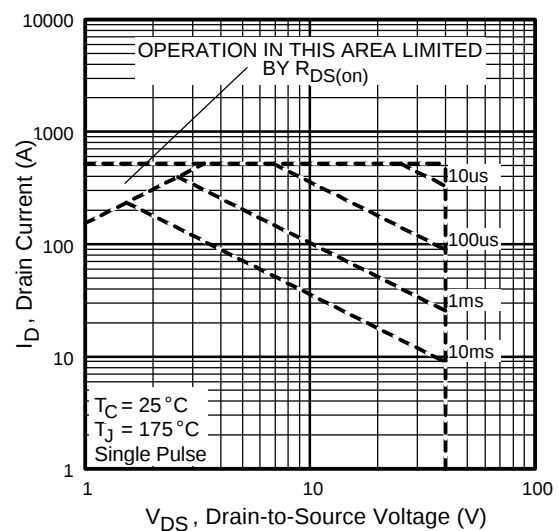


Fig 8. Maximum Safe Operating Area

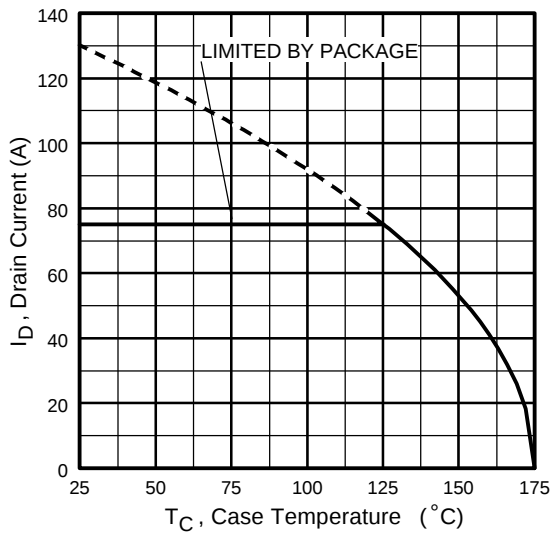


Fig 9. Maximum Drain Current Vs. Case Temperature

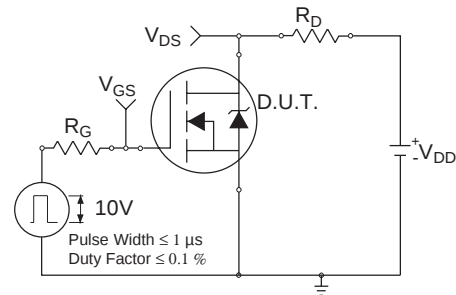


Fig 10a. Switching Time Test Circuit

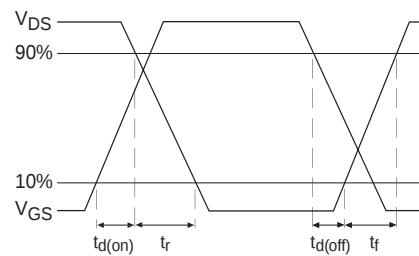


Fig 10b. Switching Time Waveforms

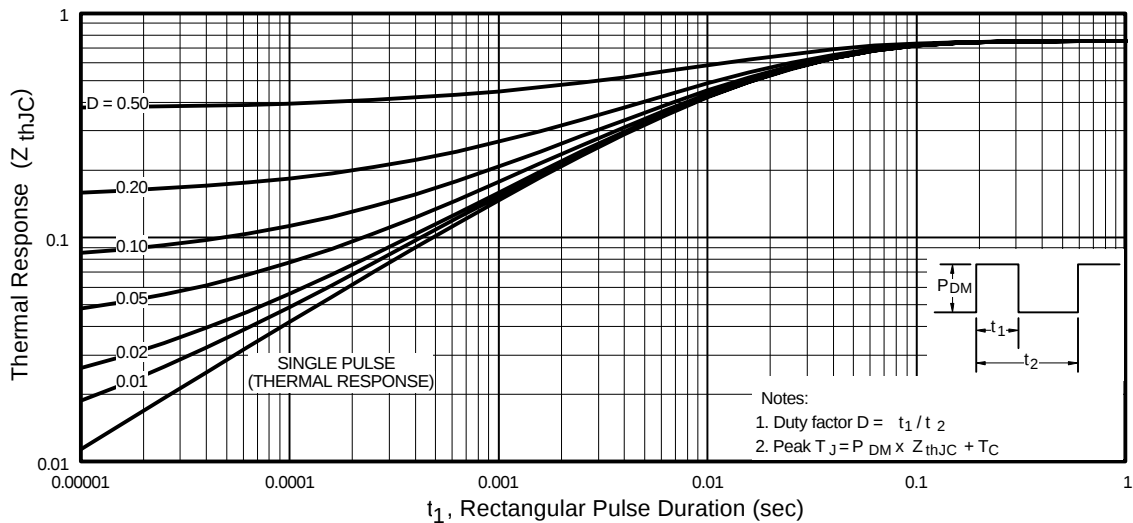


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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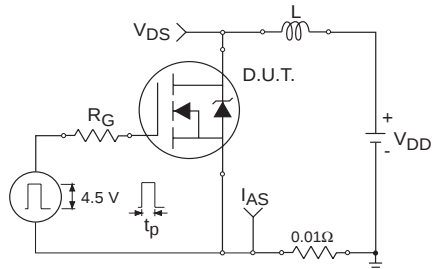


Fig 12a. Unclamped Inductive Test Circuit

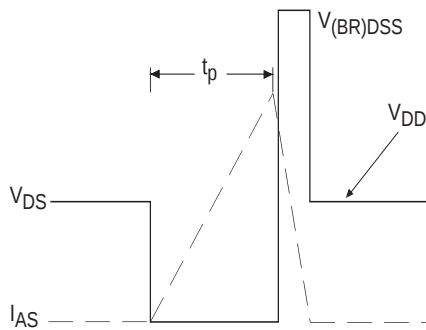


Fig 12b. Unclamped Inductive Waveforms

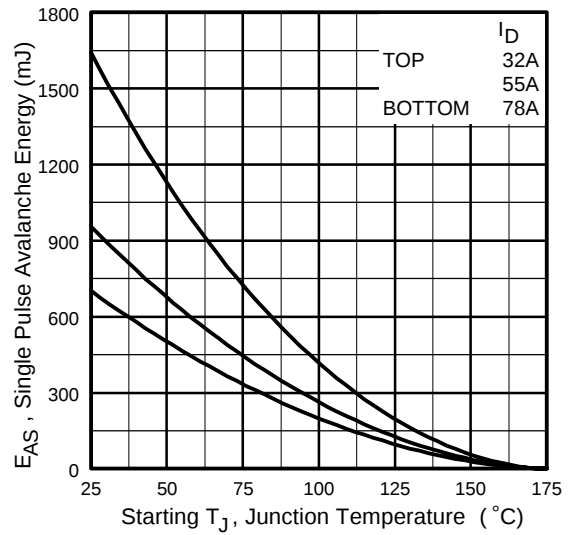


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

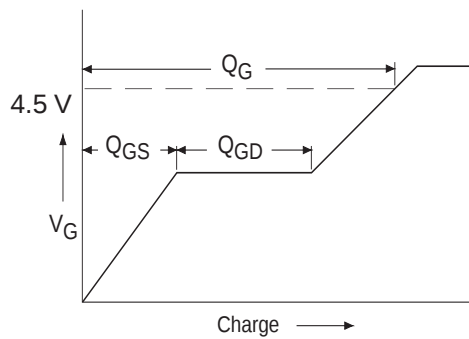


Fig 13a. Basic Gate Charge Waveform

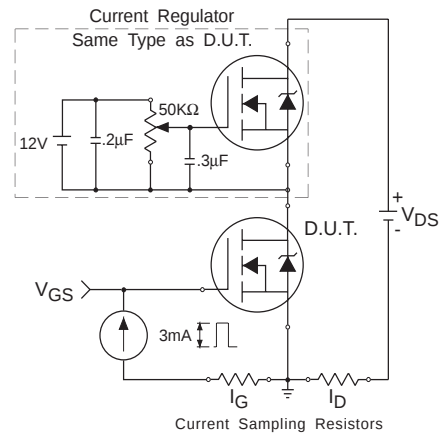


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

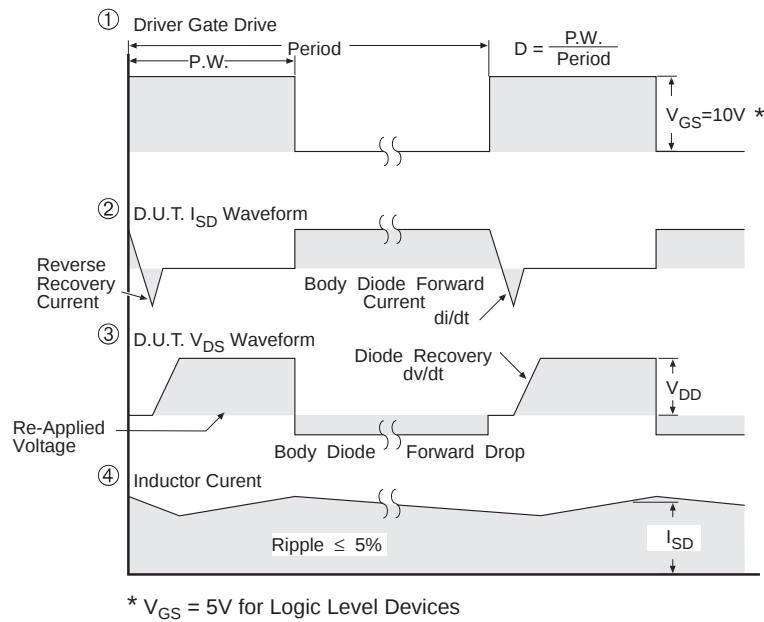
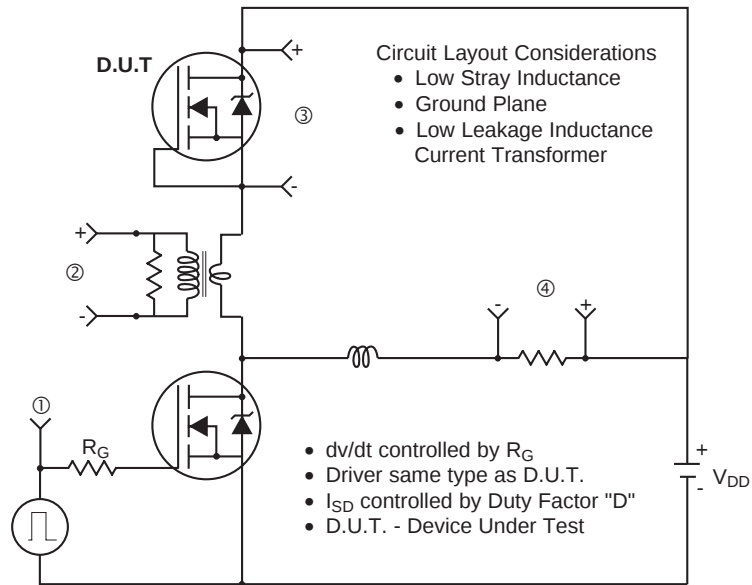
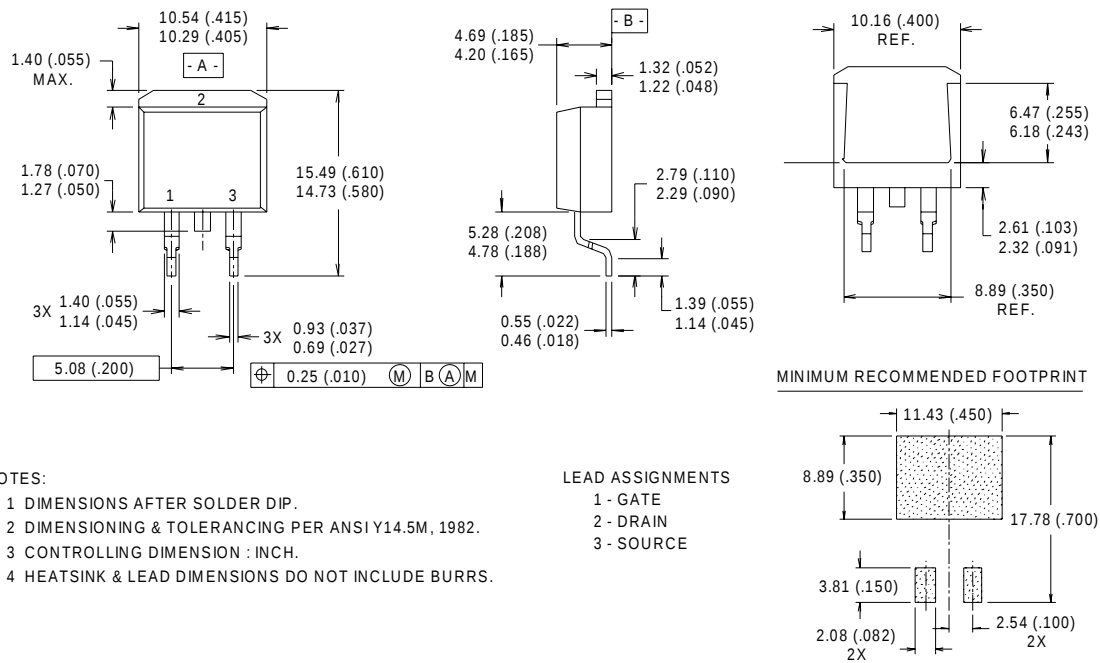


Fig 14. For N-channel HEXFET® Power MOSFETs

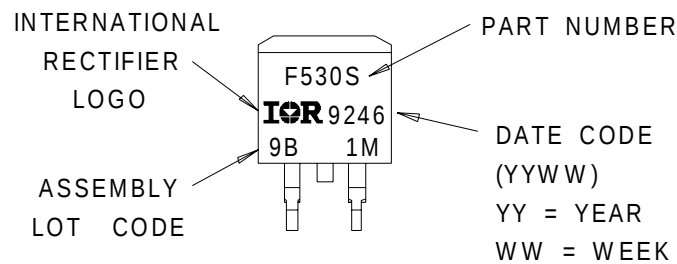
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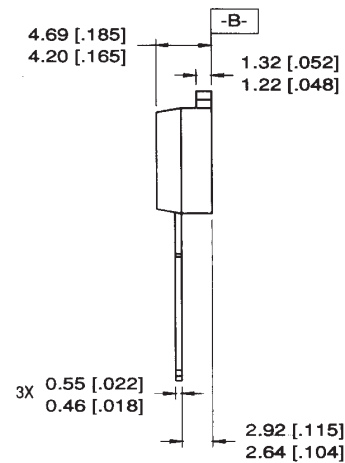
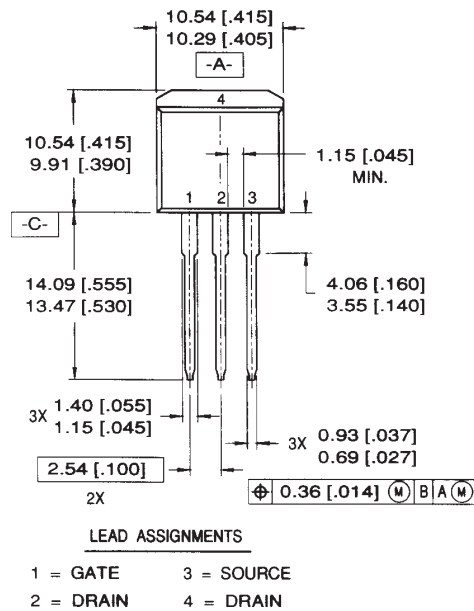
D²Pak Package Outline



D²Pak Part Marking Information



TO-262 Package Outline

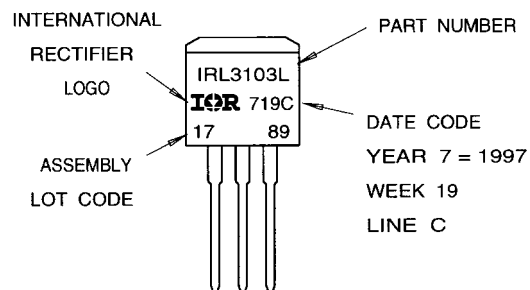


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

TO-262 Part Marking Information

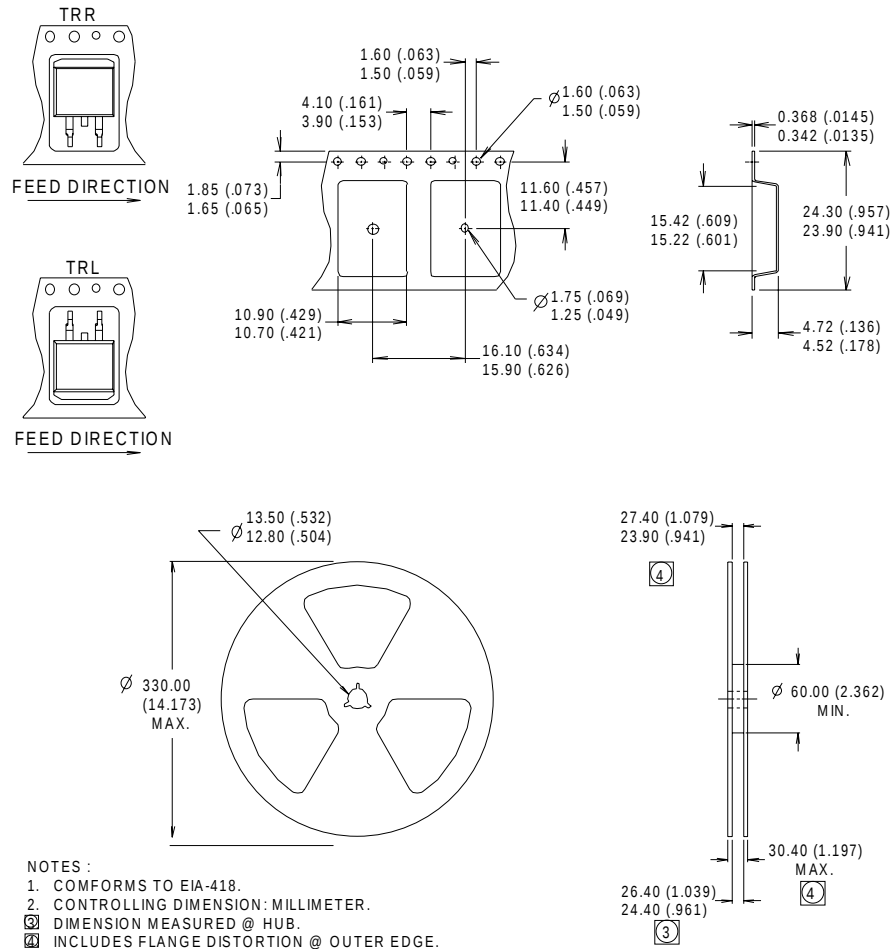
EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



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D²Pak Tape & Reel Information



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IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

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Data and specifications subject to change without notice. 12/99